

**JST131N2-600E 1A TRIAC**

Rev.A.1.1

DESCRIPTION:

The JST131N2-600E triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. Package SOT-89-2L is RoHS compliant.

MAIN FEATURES**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	600	V
RMS on-state current ($T_c = 58^\circ\text{C}$)	$I_{T(RMS)}$	1	A
Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	16.5	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		18	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	1.36	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	-	70	$\text{A}/\mu\text{s}$
		40	
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	2	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	0.5	W

Peak gate power

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33$	- -	MAX.	10	mA
				25	
V_{GT}		ALL	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k$	ALL	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	- -	MAX.	15	mA
				30	
I_H	$I_T=50mA$		MAX.	15	mA
dV/dt	$V_D=400V$ Gate Open $T_j=110$		MIN.	250	$V/\mu s$
$(dV/dt)_c$	$(dI/dt)_c=0.44A/ms$, $T_j=110$		MIN.	6	$V/\mu s$
t_{on}	$I_G=40mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25$		TYP.	3	μs
t_{off}				30	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=1.4A$ $t_p=380\mu s$	$T_j=25$	1.45	V
V_{TO}	Threshold voltage	$T_j=125$	0.96	V
R_D	Dynamic resistance	$T_j=125$	225	m
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$	5	μA
I_{RRM}		$T_j=125$	0.2	mA

THERMAL RESISTANCES

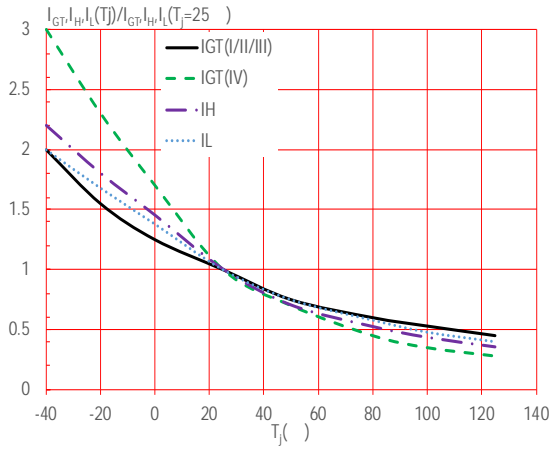
Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	50	$/W$
$R_{th(j-a)}$	junction to ambient (AC, in free air, $S=5cm^2$)	100	$/W$

FIG.1: Maximum power dissipation versus RMS on-state current



FIG.2: RMS on-state current versus case temperature

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature



ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)
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